

Device Modeling Report

COMPONENTS:
DIODE/ ENHANCED POWER LED / STANDARD
PART NUMBER: EP204K-35G1R1B1-CA
MANUFACTURER: PARA Light
EMARK: 25 degree C
COLER: BLUE

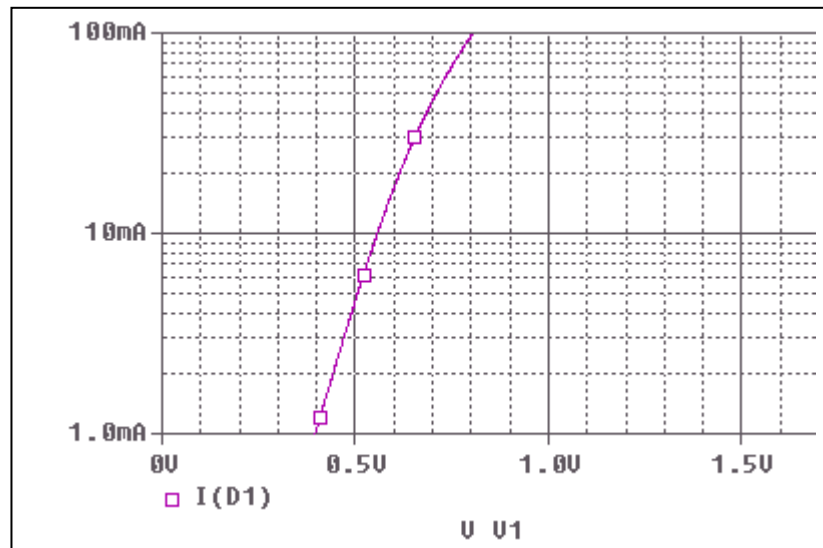


Bee Technologies Inc.

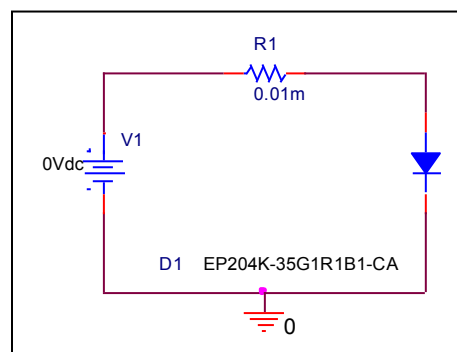
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

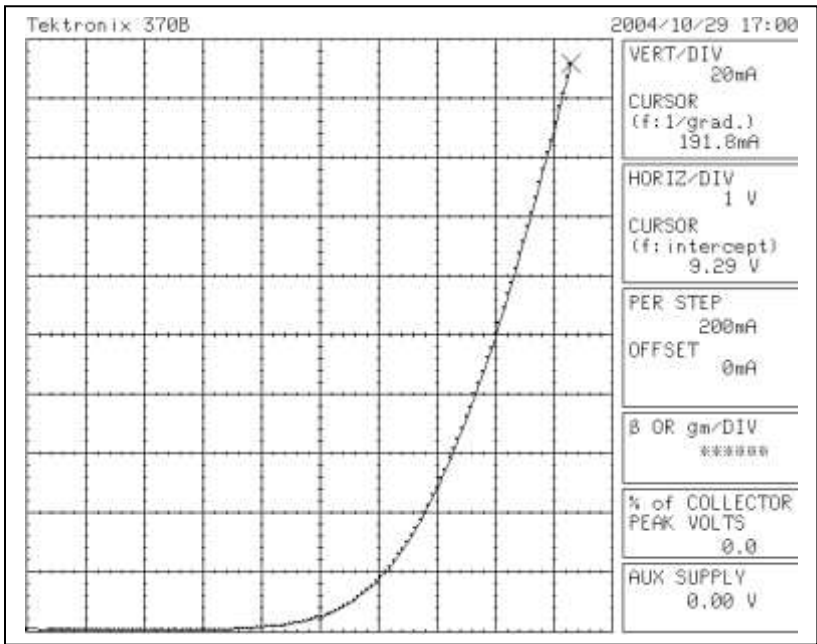


Evaluation Circuit



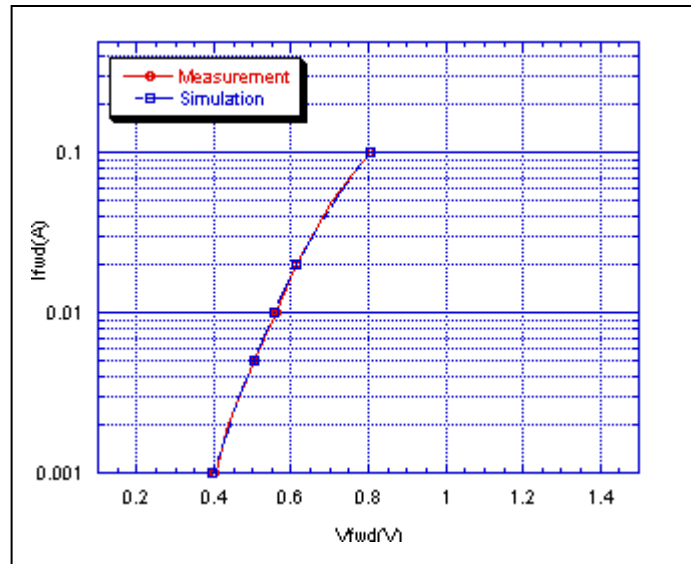
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

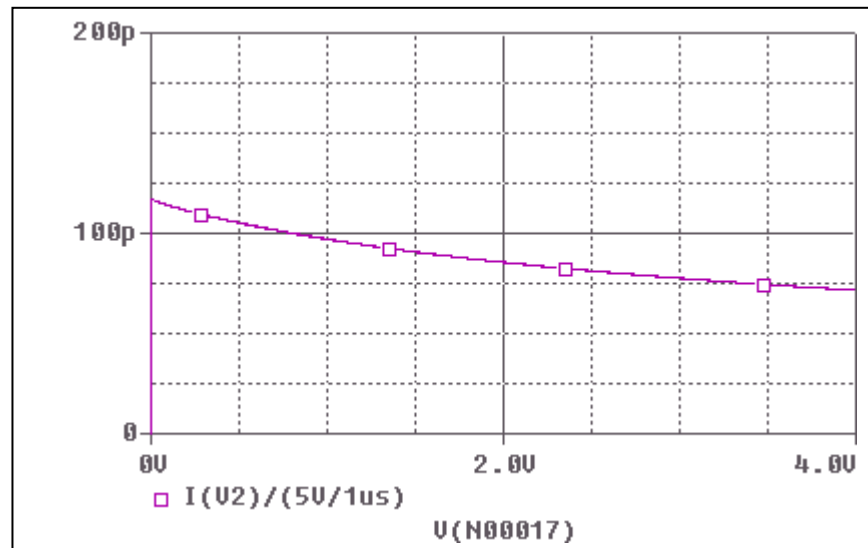


Simulation Result

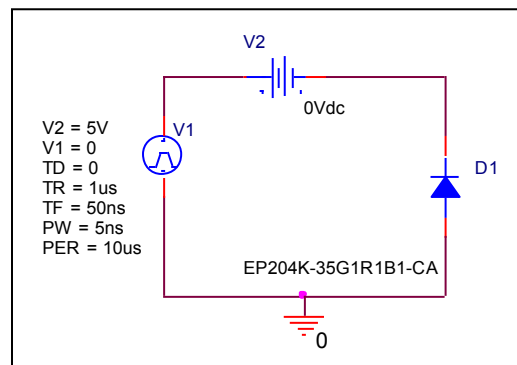
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
0.001	0.4	0.3963	0.925
0.002	0.437	0.444	1.601
0.005	0.505	0.505	0
0.01	0.559	0.554	0.894
0.02	0.616	0.6145	0.243
0.05	0.709	0.711	0.282
0.1	0.805	0.8044	0.074

Capacitance Characteristic

Circuit Simulation Result

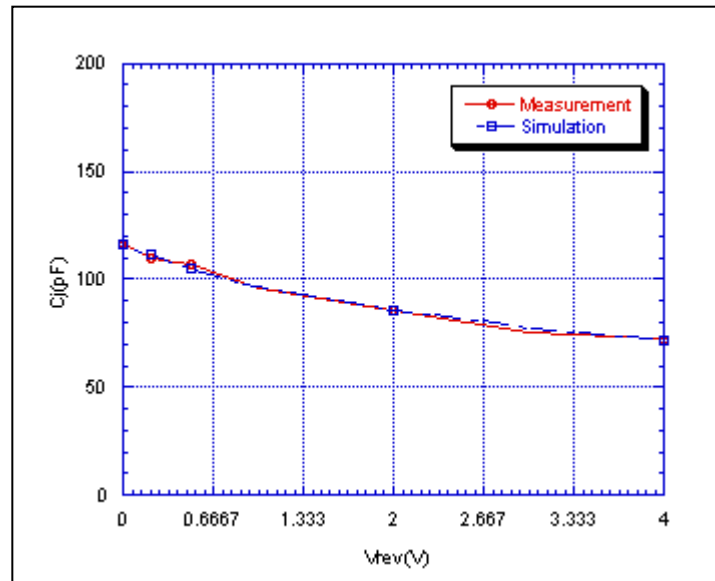


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

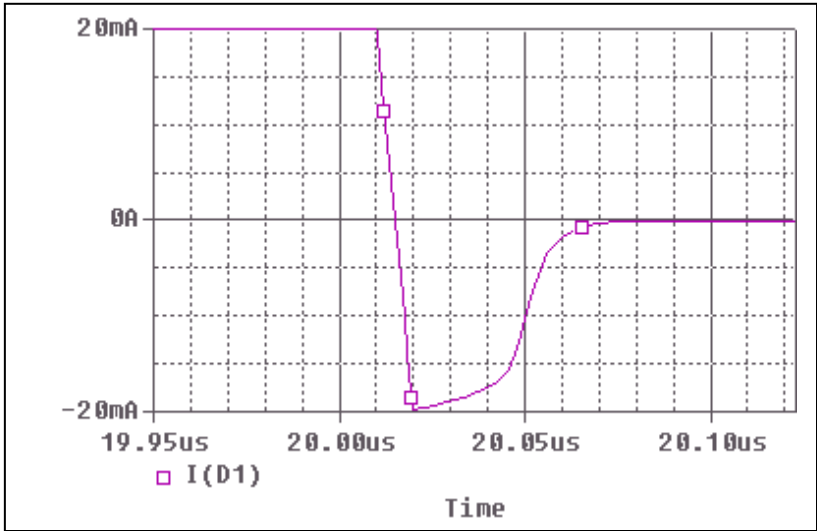


Simulation Result

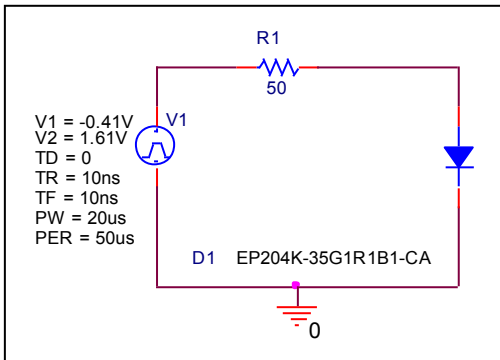
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	116.04	116.01	0.025
0.1	112.95	113.8	0.752
0.2	109.8	111.4	1.457
0.5	107.17	105.2	1.838
1	95.3	97.1	1.888
2	85.91	85.49	0.488
3	75.64	77.25	2.128
4	72.09	71.66	0.596

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

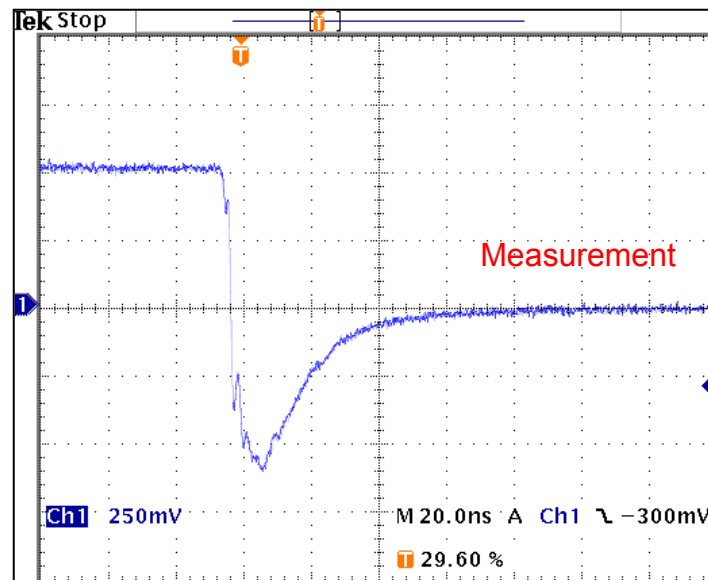


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
$T_{rr}=t_{rj}+t_{rb}$	43.2	ns	43.7	ns	1.157

Reverse Recovery Characteristic

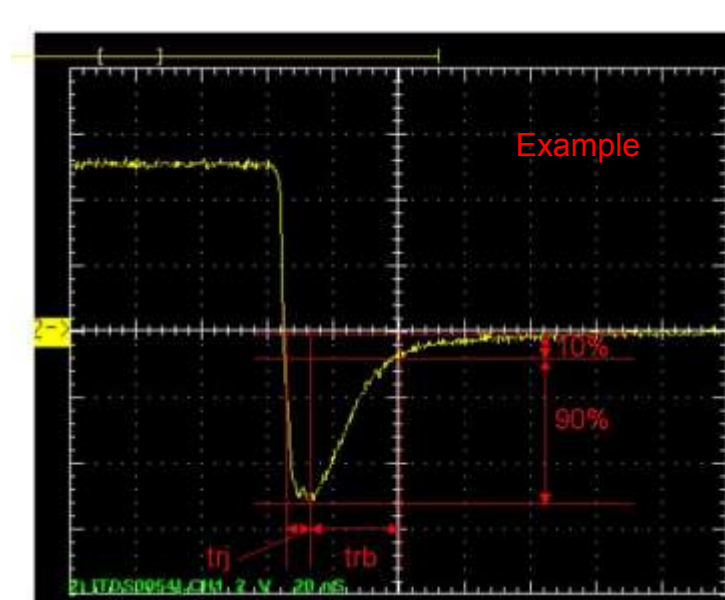
Reference



$T_{rj} = 9.60(\text{ns})$

$T_{rb} = 33.6(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}